PROCESS BATCH SHEET (Aluminum Etch) **Issue 4** **Page_____of_____**

ENSC Batch No.________________________Wafers Started____________Date__________________________
Material_________________Orientation_______________Size_______________Thickness_________________
Resistivity__________________________________Type____
Wafer Vendor_________________________Vendor Batch #___________________SFU P.O.______________

Process Step #	Process Conditions	Oper & Wafer #	Comments
_____A	**Aluminum Etch to endpoint** Transene A1 aluminum etchant. Occasional agitation. Temp = 50C. Etch rate = 100 A/sec @ 50C. Calculate etch time as a guide, but determine endpoint by eye. Inspect for endpoint at Step D.		
_____B	**DI Water Rinse** > 5 min in running DI water		
_____C	**Dry** Do not spin. Resist contaminates chuck. Blow dry with dry N2. Bake briefly in soft bake oven if required.		
_____D	**Inspect** Microscope with yellow light and measurement capability. Ensure etch complete. Etch further if needed. Measure features if required.		Measurement optional if required.
_____E	**Photoresist Strip** Soak in room temp acetone until resist is dissolved. Soak in fresh acetone for a further 1-2 min.		
_____F	**DI Water Rinse** >10 minutes in running DI water		
_____G	**Dry** Spin at max RPM until dry (false colours disappear). Check back for water. Repeat spin and/or blow dry with dry N2 if necessary.		
_____H	**Inspect** Microscope with measurement capability. Inspect for remnant resist. Repeat strip if necessary. Measure features if required.		Measurement optional if required. Remnant resist may appear as fine films or hair like structures.